Agilent MSA-0836 Cascadable Silicon Bipolar MMIC Amplifier

Data Sheet

Features

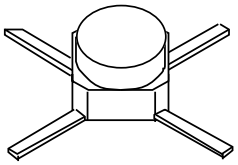
- **Usable Gain to 6.0 GHz**
- **High Gain:**
  32.5 dB Typical at 0.1 GHz
  23.0 dB Typical at 1.0 GHz
- **Low Noise Figure:**
  3.0 dB Typical at 1.0 GHz
- **Cost Effective Ceramic Microstrip Package**
- **Lead-free Option Available**

Description

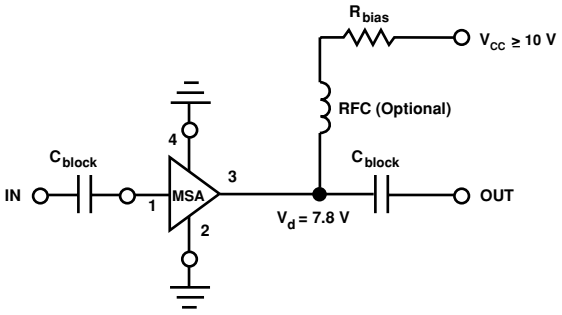
The MSA-0836 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a cost effective, microstrip package. This MMIC is designed for use as a general purpose 50 Ω gain block above 0.5 GHz and can be used as a high gain transistor below this frequency. Typical applications include narrow and moderate band IF and RF amplifiers in commercial and industrial applications.

The MSA-series is fabricated using Agilent's 10 GHz f_T, 25 GHz f_{MAX}, silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

36 micro-X Package



Typical Biasing Configuration



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MSA-0836 Absolute Maximum Ratings

Parameter	Absolute Maximum[1]
Device Current	80 mA
Power Dissipation[2,3]	750 mW
RF Input Power	+13 dBm
Junction Temperature	150°C
Storage Temperature[4]	–65°C to 150°C

Thermal Resistance[2,5]:
θ_{jc} = 175°C/W

Notes:
1. Permanent damage may occur if any of these limits are exceeded.
2. T_{CASE} = 25°C.
3. Derate at 5.7 mW/°C for T_C > 69°C.
4. Storage above +150°C may tarnish the leads of this package making it difficult to solder into a circuit.
5. The small spot size of this technique results in a higher, though more accurate determination of θ_{jc} than do alternate methods.

Electrical Specifications[1], T_A = 25°C

Symbol	Parameters and Test Conditions: I_d = 36 mA, Z_O = 50 Ω		Units	Min.	Typ.	Max.
G_P	Power Gain ($\|S_{21}\|^2$)	f = 0.1 GHz f = 1.0 GHz f = 4.0 GHz	dB	 22.0	32.5 23.0 10.5	 25.0
VSWR	Input VSWR	f = 1.0 to 3.0 GHz			2.0:1	
	Output VSWR	f = 1.0 to 3.0 GHz			1.5:1	
NF	50 Ω Noise Figure	f = 1.0 GHz	dB		3.0	
$P_{1\ dB}$	Output Power at 1 dB Gain Compression	f = 1.0 GHz	dBm		12.5	
IP_3	Third Order Intercept Point	f = 1.0 GHz	dBm		27.0	
t_D	Group Delay	f = 1.0 GHz	psec		125	
V_d	Device Voltage		V	7.0	7.8	8.4
dV/dT	Device Voltage Temperature Coefficient		mV/°C		–17.0	

Note:
1. The recommended operating current range for this device is 20 to 40 mA. Typical performance as a function of current is on the following page.

Ordering Information

Part Numbers	No. of Devices	Comments
MSA-0836-BLK	100	Bulk
MSA-0836-BLKG	100	Bulk
MSA-0836-TR1	1000	7" Reel
MSA-0836-TR1G	1000	7" Reel

Note: Order part number with a “G” suffix if lead-free option is desired.

MSA-0836 Typical Scattering Parameters[1] (Z_O = 50 Ω, T_A = 25°C, I_d = 36 mA)

Freq. GHz	S_{11}		S_{21}			S_{12}			S_{22}		k
	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang	
0.1	.63	–17	32.5	42.02	161	–37.7	.013	55	.63	–19	0.72
0.2	.58	–33	31.5	37.52	145	–33.7	.021	47	.56	–37	0.73
0.4	.49	–56	29.1	28.50	119	–29.7	.033	54	.42	–66	0.72
0.6	.40	–70	26.7	21.54	103	–27.9	.040	55	.32	–84	0.78
0.8	.35	–80	24.6	17.01	92	–26.0	.050	53	.24	–98	0.85
1.0	.33	–89	22.9	13.98	82	–24.9	.057	52	.18	–107	0.89
1.5	.30	–111	19.5	9.45	64	–22.1	.079	51	.09	–126	0.95
2.0	.30	–133	16.9	7.03	48	–20.2	.098	44	.07	–141	0.99
2.5	.32	–150	14.9	5.53	39	–19.2	.110	42	.06	–166	1.04
3.0	.34	–170	13.2	4.56	26	–18.3	.122	36	.06	–106	1.06
3.5	.38	175	11.7	3.86	14	–17.5	.133	32	.08	–100	1.08
4.0	.39	162	10.5	3.33	2	–16.7	.146	27	.12	–101	1.08
5.0	.41	132	7.9	2.47	–21	–15.6	.165	19	.21	–113	1.10
6.0	.52	95	5.8	1.94	–45	–14.6	.187	7	.20	–149	1.05

Typical Performance, T_A = 25°C

(unless otherwise noted)

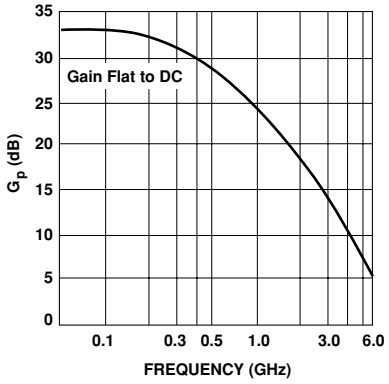


Figure 1. Typical Power Gain vs. Frequency, I_d = 36 mA.

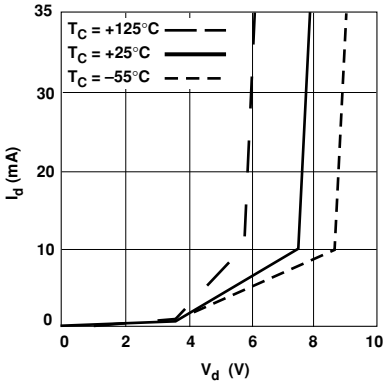


Figure 2. Device Current vs. Voltage.

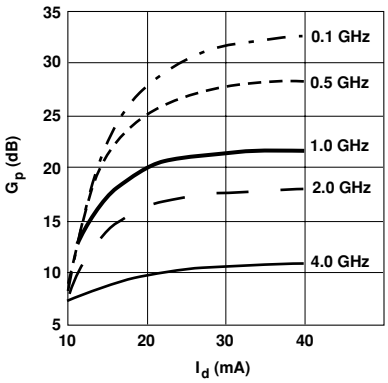


Figure 3. Power Gain vs. Current.

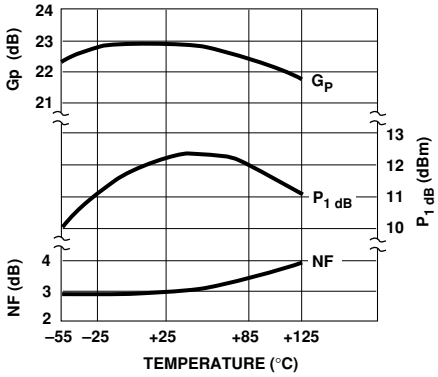


Figure 4. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Case Temperature, f = 1.0 GHz, I_d = 36 mA.

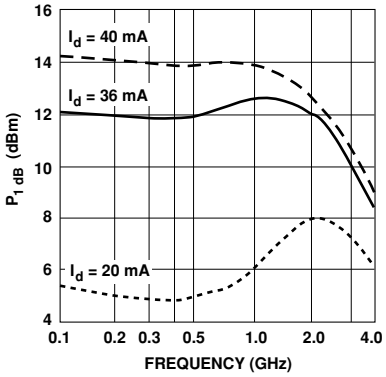


Figure 5. Output Power at 1 dB Gain Compression vs. Frequency.

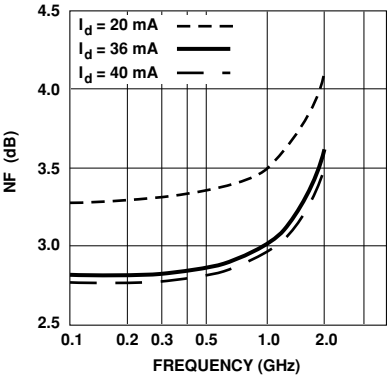
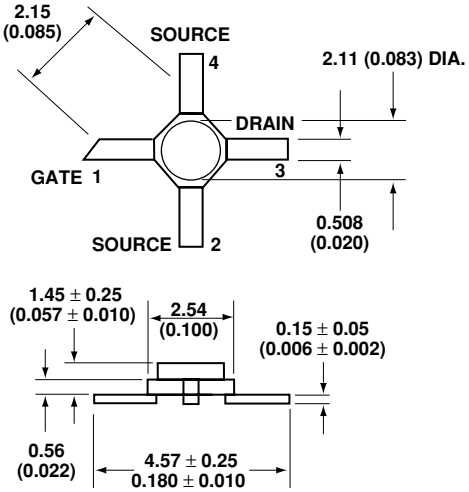


Figure 6. Noise Figure vs. Frequency.

36 micro-X Package Dimensions



Notes:
1. **Dimensions are in millimeters (inches)**
2. **Tolerances: in .xxx = ± 0.005**
   mm .xx = ± 0.13

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Data subject to change.

Obsoletes 5988-4741E
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5989-2742EN

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